

isc N-Channel MOSFET Transistor

IPD80R1K0CE,IIPD80R1K0CE

FEATURES

- Static drain-source on-resistance:
 $R_{DS(on)} \leq 0.95 \Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

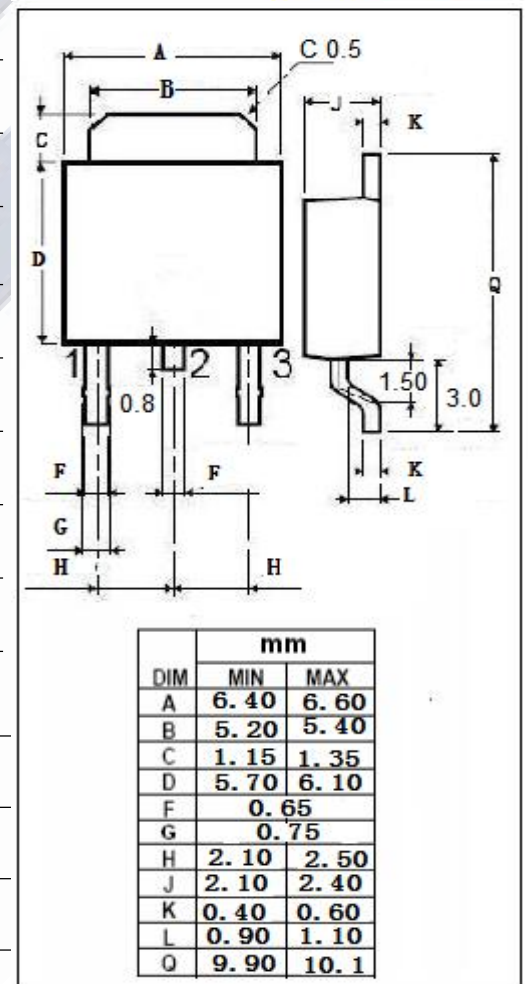
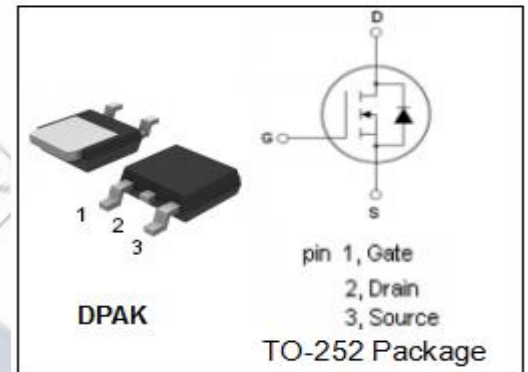
- High peak current capability

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	800	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	5.7	A
I_{DM}	Drain Current-Single Pulsed	18	A
P_D	Total Dissipation @ $T_c=25^\circ\text{C}$	83	W
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Channel-to-case thermal resistance	1.5	$^\circ\text{C/W}$
$R_{th(j-a)}$	Channel-to-ambient thermal resistance	62	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=0.25mA$	800			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.25mA$	2.1		3.9	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=3.6A$			0.95	Ω
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=20V; V_{DS}=0V$			0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=800V; V_{GS}=0V$			10	μA
V_{SD}	Diode forward voltage	$I_F=5.7A, V_{GS}=0V$			1.2	V